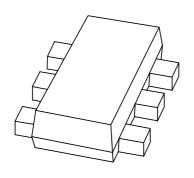
#### **DISCRETE SEMICONDUCTORS**

# DATA SHEET



### PEMB9

PNP resistor-equipped transistors R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$ 

Product specification

2003 Jan 07





### PNP resistor-equipped transistors R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$

#### PEMB9

#### **FEATURES**

- 300 mW total power dissipation
- Very small 1.6 mm  $\times$  1.2 mm  $\times$  0.55 mm ultra thin package
- Excellent coplanarity due to straight leads
- Replaces two SC-75/SC-89 packaged transistors on same PCB area
- Reduces required PCB area
- Reduced pick and place costs.

#### **APPLICATIONS**

- · General purpose switching and amplification
- · Inverter and interface circuits
- · Circuit driver.

#### **DESCRIPTION**

PNP resistor-equipped transistors in a SOT666 plastic package.

#### **MARKING**

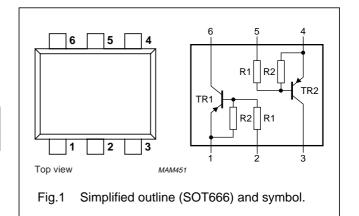
TYPE NUMBER	MARKING CODE
PEMB9	Z6

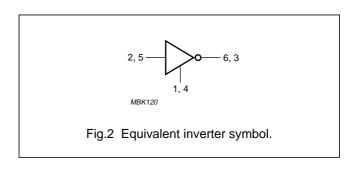
#### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	-50	V
I <sub>CM</sub>	peak collector current	-100	mA
TR1	PNP	_	_
TR2	PNP	_	_
R1	bias resistor	10	kΩ
R2	bias resistor	47	kΩ

#### **PINNING**

PIN	DESCRIPTION		
1, 4	emitter	TR1; TR2	
2, 5	base	TR1; TR2	
6, 3	collector	TR1; TR2	





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#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT	
Per transis	Per transistor unless otherwise specified					
V <sub>CBO</sub>	collector-base voltage	open emitter	_	-50	V	
V <sub>CEO</sub>	collector-emitter voltage	open base	_	-50	V	
V <sub>EBO</sub>	emitter-base voltage	open collector	-	-10	V	
VI	input voltage					
	positive		_	+40	V	
	negative		_	-6	V	
I <sub>O</sub>	output current (DC)		-	-100	mA	
I <sub>CM</sub>	peak collector current		-	-100	mA	
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	-	200	mW	
T <sub>stg</sub>	storage temperature		-65	+150	°C	
Tj	junction temperature		-	150	°C	
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C	
Per device	•	•	•		•	
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	_	300	mW	

#### Note

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	in free air; notes 1 and 2	416	K/W

#### **Notes**

- 1. Transistor mounted on an FR4 printed-circuit board.
- 2. The only recommended soldering method is reflow soldering.

<sup>1.</sup> Transistor mounted on a FR4 printed-circuit board.

# PNP resistor-equipped transistors R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$

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#### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER CONDITIONS		MIN.	TYP.	MAX.	UNIT
Per transis	Per transistor unless otherwise specified					
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_{C} = 0$	_	_	-100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	$V_{CE} = -50 \text{ V}; I_B = 0$	_	_	-1	μΑ
		$V_{CE} = -30 \text{ V}; I_{B} = 0; T_{j} = 150 ^{\circ}\text{C}$	_	_	-50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0$	_	_	-150	μΑ
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA}$	-100	_	_	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = -5 \text{ mA}; I_B = -0.25 \text{ mA}$	_	_	-100	mV
V <sub>i(off)</sub>	input off voltage	$V_{CE} = -5 \text{ V}; I_{C} = -100 \mu\text{A}$	_	-0.7	-0.5	V
V <sub>i(on)</sub>	input on voltage	$V_{CE} = -0.3 \text{ V; } I_{C} = -5 \text{ mA}$	-1.4	-0.8	_	V
R1	input resistor		7	10	13	kΩ
R2 R1	resistor ratio		3.7	4.7	5.7	
C <sub>c</sub>	collector capacitance	$I_E = I_e = 0$ ; $V_{CB} = -10 \text{ V}$ ; $f = 1 \text{ MHz}$	_	_	3	pF

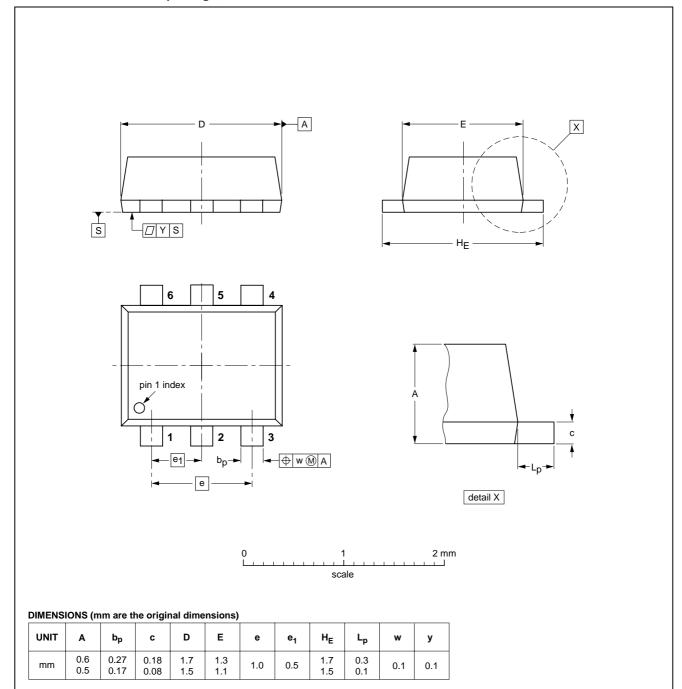
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#### **PACKAGE OUTLINE**

Plastic surface mounted package; 6 leads

**SOT666** 



OUTLINE	REFERENCES			EUROPEAN	ICCUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT666						<del>-01-01-04</del> 01-08-27

### PNP resistor-equipped transistors R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$

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#### **DATA SHEET STATUS**

LEVEL	DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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#### **NOTES**

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#### **Contact information**

For additional information please visit http://www.semiconductors.philips.com. Fax: +31 40 27 24825 For sales offices addresses send e-mail to: sales.addresses@www.semiconductors.philips.com.

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